

NSS60600MZ4, NSV60600MZ4T1G, NSV60600MZ4T3G

60 V, 6.0 A, Low $V_{CE(sat)}$ PNP Transistor

ON Semiconductor's e²PowerEdge family of low $V_{CE(sat)}$ transistors are surface mount devices featuring ultra low saturation voltage ($V_{CE(sat)}$) and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Typical applications are DC-DC converters and power management in portable and battery powered products such as cellular and cordless phones, PDAs, computers, printers, digital cameras and MP3 players. Other applications are low voltage motor controls in mass storage products such as disc drives and tape drives. In the automotive industry they can be used in air bag deployment and in the instrument cluster. The high current gain allows e²PowerEdge devices to be driven directly from PMU's control outputs, and the Linear Gain (Beta) makes them ideal components in analog amplifiers.

Features

- AEC-Q101 Qualified and PPAP Capable
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant*

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V_{CEO}	-60	Vdc
Collector-Base Voltage	V_{CBO}	-100	Vdc
Emitter-Base Voltage	V_{EBO}	-6.0	Vdc
Collector Current - Continuous	I_C	-6.0	A
Collector Current - Peak	I_{CM}	-12.0	A

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



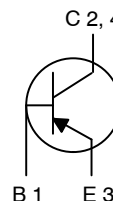
ON Semiconductor®

<http://onsemi.com>

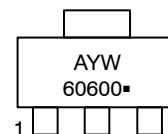
**-60 VOLTS, 6.0 AMPS
2.0 WATTS
PNP LOW $V_{CE(sat)}$ TRANSISTOR
EQUIVALENT $R_{DS(on)} 50\text{ m}\Omega$**



**SOT-223
CASE 318E
STYLE 1**

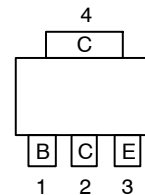


MARKING DIAGRAM



A = Assembly Location
Y = Year
W = Work Week
60600 = Specific Device Code
▪ = Pb-Free Package

PIN ASSIGNMENT



Top View Pinout

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D (Note 1)	800 6.5	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$ (Note 1)	155	$^\circ\text{C}/\text{W}$
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D (Note 2)	2 15.6	W mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$ (Note 2)	64	$^\circ\text{C}/\text{W}$
Total Device Dissipation (Single Pulse < 10 sec.)	$P_{D\text{single}}$ (Note 3)	710	mW
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

1. FR-4 @ 7.6 mm², 1 oz. copper traces.
2. FR-4 @ 645 mm², 1 oz. copper traces.
3. Thermal response.

ORDERING INFORMATION

Device	Package	Shipping [†]
NSS60600MZ4T1G	SOT-223 (Pb-Free)	1,000 / Tape & Reel
NSV60600MZ4T1G	SOT-223 (Pb-Free)	1,000 / Tape & Reel
NSS60600MZ4T3G	SOT-223 (Pb-Free)	4,000 / Tape & Reel
NSV60600MZ4T3G	SOT-223 (Pb-Free)	4,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NSS60600MZ4, NSV60600MZ4T1G, NSV60600MZ4T3G

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector – Emitter Breakdown Voltage ($I_C = -10\text{ mA}$, $I_B = 0$)	$V_{(BR)CEO}$	-60	–	–	Vdc
Collector – Base Breakdown Voltage ($I_C = -0.1\text{ mA}$, $I_E = 0$)	$V_{(BR)CBO}$	-100	–	–	Vdc
Emitter – Base Breakdown Voltage ($I_E = -0.1\text{ mA}$, $I_C = 0$)	$V_{(BR)EBO}$	-6.0	–	–	Vdc
Collector Cutoff Current ($V_{CB} = -100\text{ Vdc}$, $I_E = 0$)	I_{CBO}	–	–	-0.1	μA
Emitter Cutoff Current ($V_{EB} = -6.0\text{ Vdc}$)	I_{EBO}	–	–	-0.1	μA

ON CHARACTERISTICS

DC Current Gain (Note 4) ($I_C = -500\text{ mA}$, $V_{CE} = -2.0\text{ V}$) ($I_C = -1.0\text{ A}$, $V_{CE} = -2.0\text{ V}$) ($I_C = -2.0\text{ A}$, $V_{CE} = -2.0\text{ V}$) ($I_C = -6.0\text{ A}$, $V_{CE} = -2.0\text{ V}$)	h_{FE}	150 120 100 70	– – – –	– 360 – –	–
Collector – Emitter Saturation Voltage (Note 4) ($I_C = -0.1\text{ A}$, $I_B = -2.0\text{ mA}$) ($I_C = -1.0\text{ A}$, $I_B = -0.100\text{ A}$) ($I_C = -2.0\text{ A}$, $I_B = -0.200\text{ A}$) ($I_C = -3.0\text{ A}$, $I_B = -60\text{ mA}$) ($I_C = -6.0\text{ A}$, $I_B = -0.6\text{ A}$)	$V_{CE(sat)}$	– – – – –	– -0.050 -0.100 – –	-0.050 -0.070 -0.120 -0.250 -0.350	V
Base – Emitter Saturation Voltage (Note 4) ($I_C = -1.0\text{ A}$, $I_B = -0.1\text{ A}$)	$V_{BE(sat)}$	–	–	-1.0	V
Base – Emitter Turn-on Voltage (Note 4) ($I_C = -1.0\text{ A}$, $V_{CE} = -2.0\text{ V}$)	$V_{BE(on)}$	–	–	-0.900	V
Cutoff Frequency ($I_C = -500\text{ mA}$, $V_{CE} = -10\text{ V}$, $f = 1.0\text{ MHz}$)	f_T	100	–	–	MHz
Input Capacitance ($V_{EB} = 5.0\text{ V}$, $f = 1.0\text{ MHz}$)	C_{ibo}	–	360	–	pF
Output Capacitance ($V_{CB} = 10\text{ V}$, $f = 1.0\text{ MHz}$)	C_{obo}	–	60	–	pF

SWITCHING CHARACTERISTICS

Delay ($V_{CC} = -30\text{ V}$, $I_C = 750\text{ mA}$, $I_{B1} = 15\text{ mA}$)	t_d	–	100	–	ns
Rise ($V_{CC} = -30\text{ V}$, $I_C = 750\text{ mA}$, $I_{B1} = 15\text{ mA}$)	t_r	–	180	–	ns
Storage ($V_{CC} = -30\text{ V}$, $I_C = 750\text{ mA}$, $I_{B1} = 15\text{ mA}$)	t_s	–	540	–	ns
Fall ($V_{CC} = -30\text{ V}$, $I_C = 750\text{ mA}$, $I_{B1} = 15\text{ mA}$)	t_f	–	145	–	ns

4. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle $\leq 2\%$.

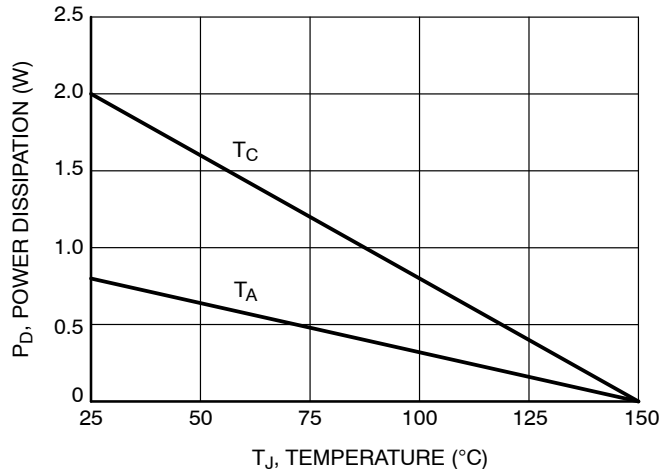


Figure 1. Power Derating

TYPICAL CHARACTERISTICS

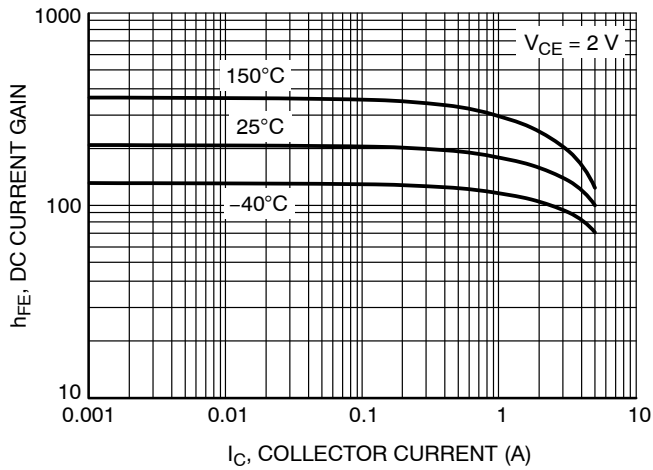


Figure 2. DC Current Gain

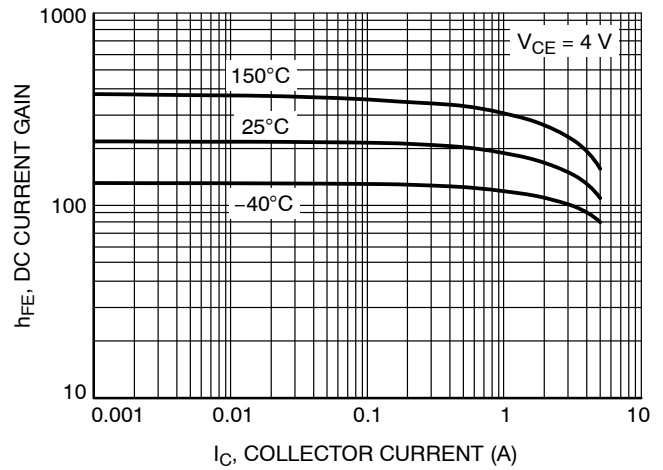


Figure 3. DC Current Gain

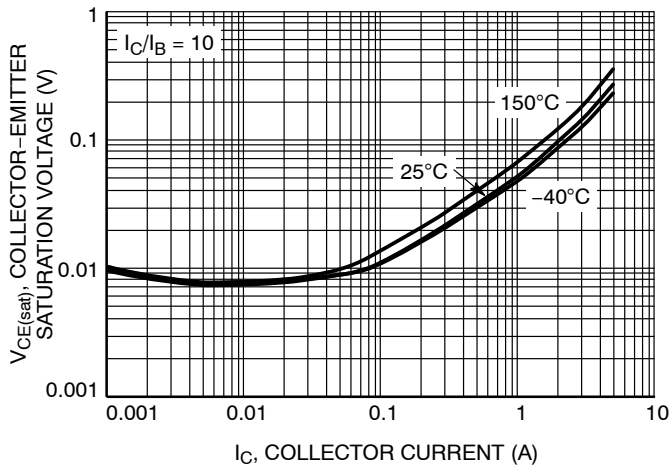


Figure 4. Collector-Emitter Saturation Voltage

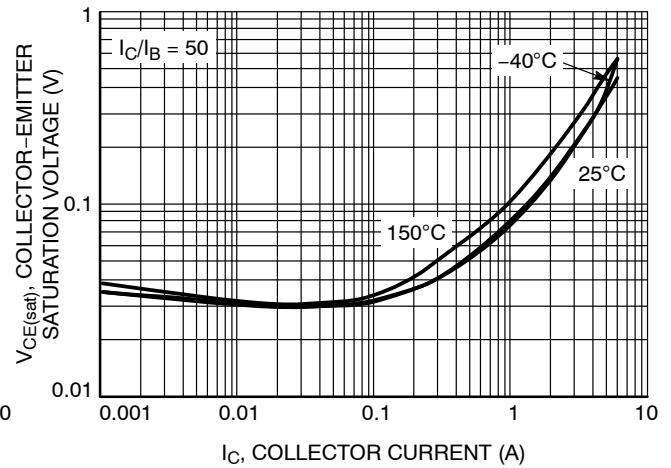


Figure 5. Collector-Emitter Saturation Voltage

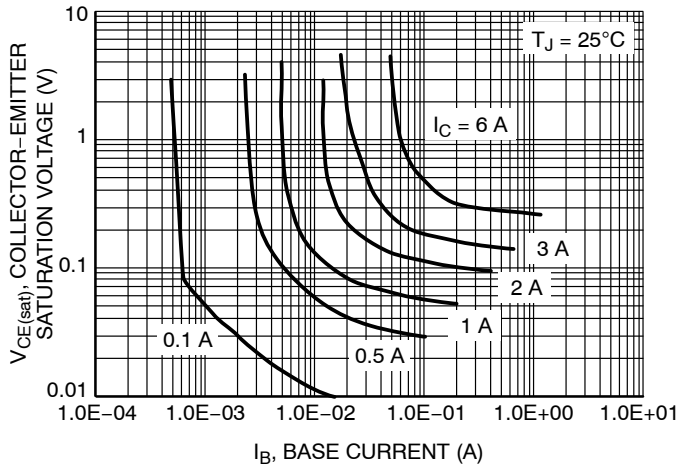


Figure 6. Collector Saturation Region

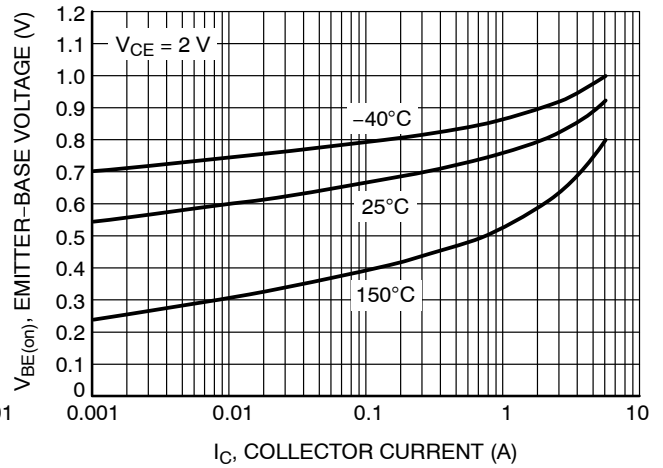


Figure 7. $V_{BE(on)}$ Voltage

TYPICAL CHARACTERISTICS

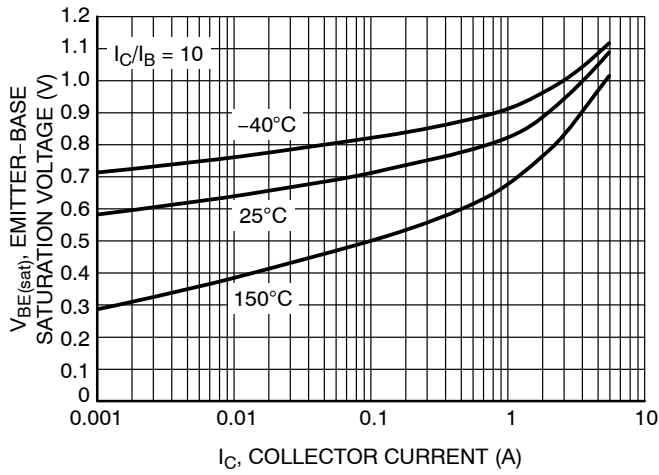


Figure 8. Base-Emitter Saturation Voltage

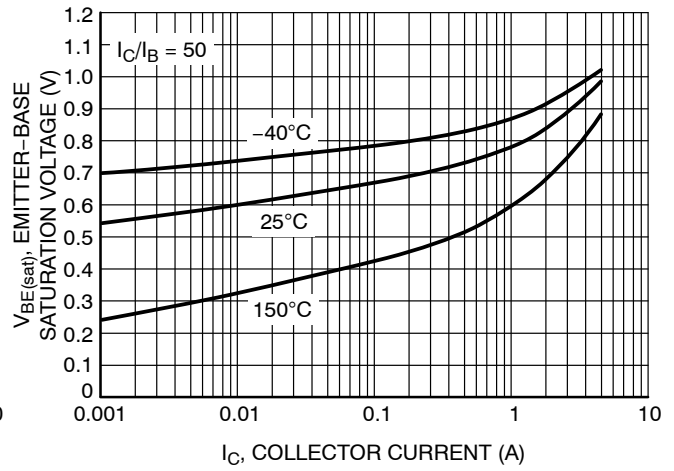


Figure 9. Base-Emitter Saturation Voltage

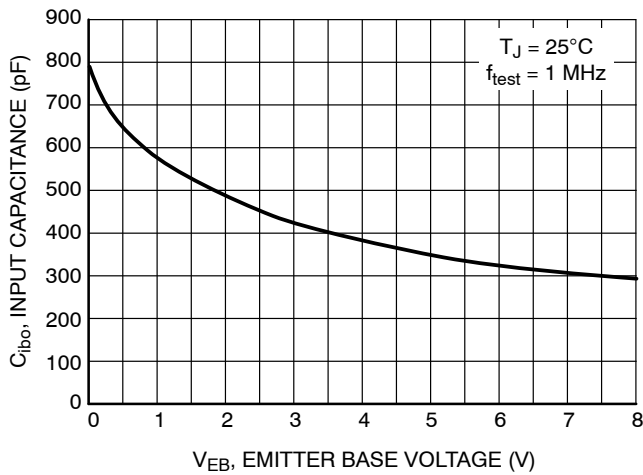


Figure 10. Input Capacitance

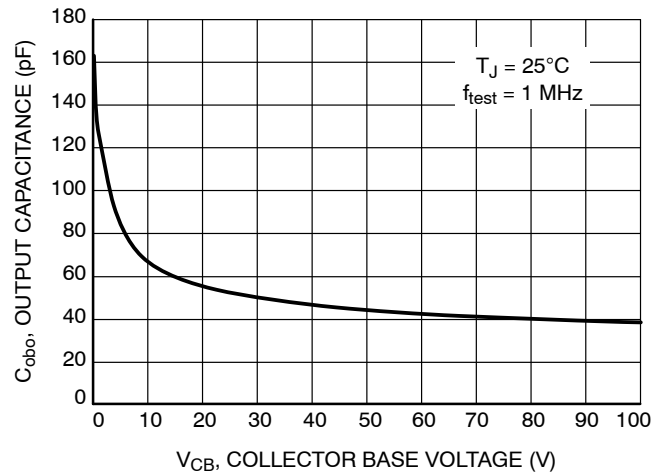


Figure 11. Output Capacitance

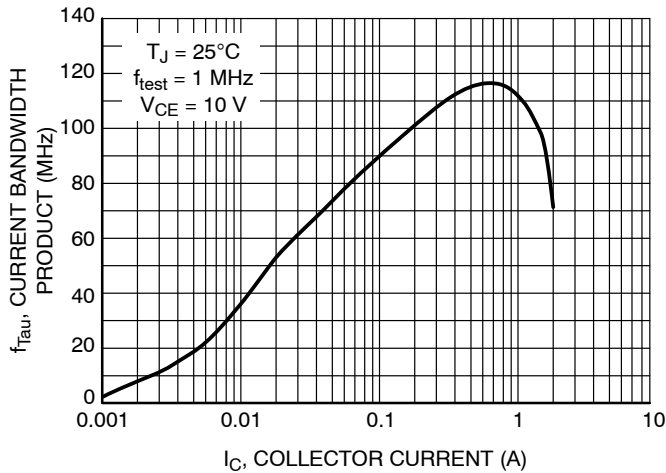


Figure 12. Current-Gain Bandwidth Product

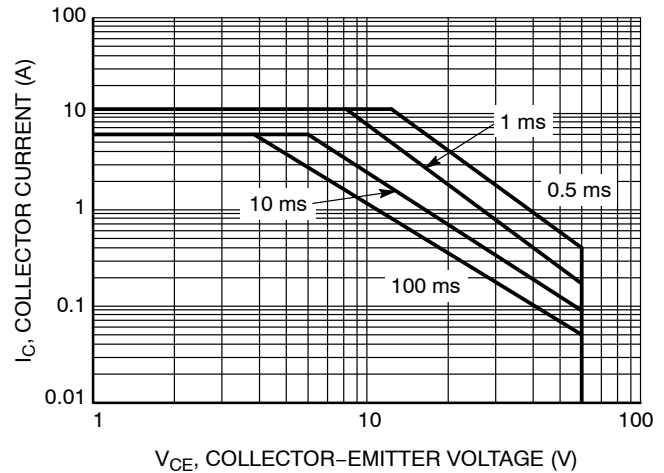


Figure 13. Safe Operating Area

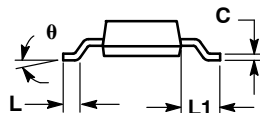
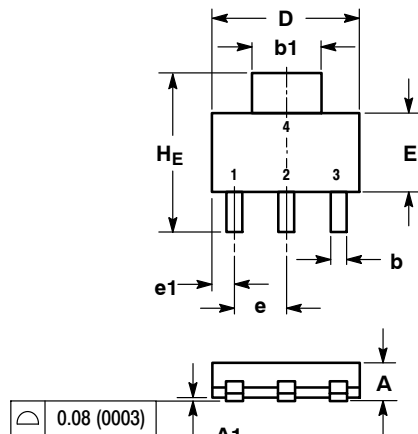
NSS60600MZ4, NSV60600MZ4T1G, NSV60600MZ4T3G

PACKAGE DIMENSIONS

SOT-223 (TO-261)

CASE 318E-04

ISSUE N



NOTES:

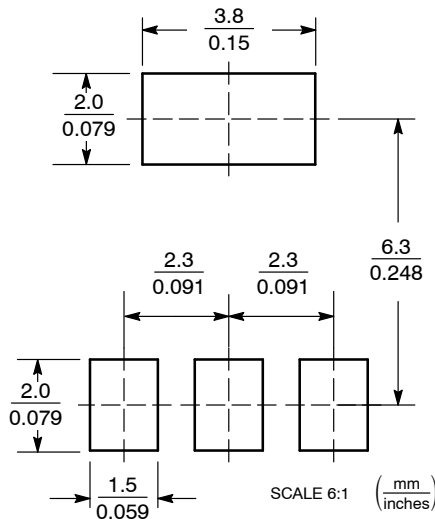
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.50	1.63	1.75	0.060	0.064	0.068
A1	0.02	0.06	0.10	0.001	0.002	0.004
b	0.60	0.75	0.89	0.024	0.030	0.035
b1	2.90	3.06	3.20	0.115	0.121	0.126
c	0.24	0.29	0.35	0.009	0.012	0.014
D	6.30	6.50	6.70	0.249	0.256	0.263
E	3.30	3.50	3.70	0.130	0.138	0.145
e	2.20	2.30	2.40	0.087	0.091	0.094
e1	0.85	0.94	1.05	0.033	0.037	0.041
L	0.20	---	---	0.008	---	---
L1	1.50	1.75	2.00	0.060	0.069	0.078
HE	6.70	7.00	7.30	0.264	0.276	0.287
θ	0°	---	10°	0°	---	10°

STYLE 1:

- PIN 1: BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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NSS60600MZ4/D



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- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
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- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
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- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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